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TT Electronics/Optek Technology OP505A

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Datasheet of OP505A - PHOTOTRANSISTOR IR 3MM 935NM NPN

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NPN Silicon Phototransistor

OP505, OP506, OP535 & OP705 Series



Features:

- T-1 package style
- · Variety of sensitivity ranges
- Choice of narrow or wide receiving angle
- Small package size ideal for space-limited applications
- 0.050" [1.27mm] or 0.100" [2.54mm] Lead spacing



Description:

Each **OP505** and **OP506** devices consist of an NPN silicon phototransistor, the OP535 device consist of an NPN silicon photodarlington transistor and the OP705 device consist of an NPN silicon phototransistor with a large value resistor integrated between the Base and Emitter for low light signal rejection. All of the devices are molded in a blue-tinted T-1 (3mm) epoxy package

The **OP505**, **OP535** and **OP705** devices have a narrow receiving angle (typically 25°) that provides excellent on-axis coupling while the **OP506** device has a wider receiving angle (typically 60°) for those applications where a narrow receiving angle of the **OP505**, **OP535** and **OP705** is not required. The **OP505W** and **OP506W** device have the widest receiving angle (typically 90°) and provides relatively even reception over a large area.

Devices are 100% production tested, using infrared light for close correlation with Optek's GaAs and GaAlAs emitters.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Please see your OPTEK representative for custom versions of these devices.

Applications:

- Space-limited applications
- Interruptive applications to detect media which is semitransparent to infrared light

	Order	ring Inform	ation	
Part Number	Sensor	Viewing Angle	Lead Spacing	Lead Length
OP505A				
OP505B		25°	0.050%	
OP505C		23	0.050" [1.27 mm]	
OP505D	,		[2.27]	
OP505W	Transistor	90°		
OP506A	11 011313101			
OP506B		60°	0.100"	
OP506C		00	[2.54 mm]	0.50"
OP506D			[2.5 :]	[12.7 mm] (all devices in
OP506W		90°		series)
OP535A				
OP535B	Darlington			
OP535C			0.050%	
OP705A	,	25°	0.050" [1.27 mm]	
OP705B	R_{BE}		[1.27	
OP705C	Transistor			
OP705D				



General Note

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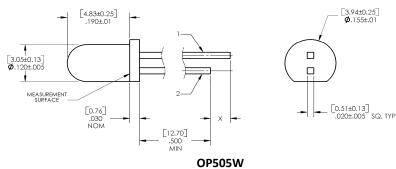
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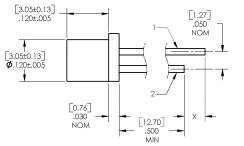
NPN Silicon Phototransistor

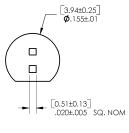
OP505, OP506, OP535 & OP705 Series



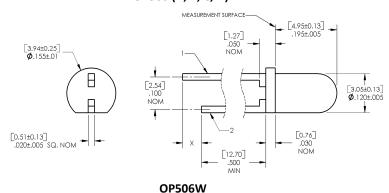
OP505, OP535 & OP705 (A, B, C, D)

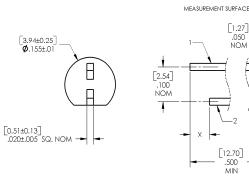


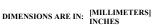


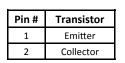


OP506 (A, B, C, D)



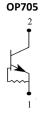


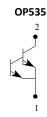












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To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK'S molded plastics.

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[0.76]

.030 MOM

[3.05±0.13] - .120±.005

> 3.05±0.13 Ø.120±.005

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Datasheet of OP505A - PHOTOTRANSISTOR IR 3MM 935NM NPN

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NPN Silicon Phototransistor

OP505, OP506, OP535 & OP705 Series



Electrical Specifications

Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)	
Storage & Operating Temperature Range	-40°C to +100° C
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage (OP505 and OP506 series only)	5.0 V
Lead Soldering Temperature (1/16 inch (1.6 mm) from case for 5 seconds with soldering iron)	260° C
Power Dissipation	100 mW ⁽²⁾
Emitter Reverse Current (OP705 series only)	10 mA
Collector DC Current (OP705 series only)	30 mA

Electrical Characteristics (T_A = 25° C unless otherwise noted) **OP505**, **OP506**, **OP705** Series

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
	On-State Collector Current					
	OP505A, OP506A	4.30	-	-		
	OP705A	3.95	-	12.00		
	OP705B	2.65	-	7.25		
	OP505B, OP506B	2.15	-	5.95	mA	$V_{CE} = 5 \text{ V}, E_e = 0.50 \text{ mW/cm}^{2(3)}$
$I_{C(ON)}$	OP705C	1.50	-	4.85		
	OP705D	1.50	-	12.00		
	OP505C, OP506C	1.10	-	3.00		
	OP505D, OP506D	0.55	-	-		
	OP505W, OP506W	0.10	-	-	mA	$V_{CE} = 5 \text{ V, } E_e = 0.13 \text{ mW/cm}^{2(3)}$
I _{CEO}	Collector-Dark Current	-	-	100	nA	V _{CE} = 10 V, E _E = 0 ⁽⁴⁾
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage OP505, OP505W, OP506, OP506W OP705	30 24	- -		V	Ι _C = 100 μΑ
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	Ι _Ε = 100 μΑ
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	-	-	0.40	V	$I_C = 250 \mu\text{A}, E_E = 0.5 \text{mW/cm}^{2(2)}$
ΔΙ _C /ΔΤ	Relative I _C Changes with Temperature	-	1.00	-	%/°C	$V_{CE} = 5 \text{ V, } E_E = 1.0 \text{ mW/cm}^2$
E _{KP}	Knee Point Irradiance OP705	-	0.02	-	mW/cm ²	V _{CE} = 5 V ⁽⁵⁾
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	V _{CE} = 10 V, E _E = 0
I _{ECO}	Emitter-Collector Reverse Current	-	-	100	μΑ	V _{CE} = 5 V, E _E = 0

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.
- (2) Derate linearly 1.33 mW/° C above 25° C.
- (3) Light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm and a radiometric intensity level, which varies less than 10% over the entire lens surface of the phototransistor being tested.
- (4) For OP505, OP505W, OP506, OP506W and OP705, to calculate typical collector dark current in nA, use the formula $I_{CED} = 10^{(0.040T_A^{-3.4})}$ where T_A is ambient temperature in ° C.

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NPN Silicon Phototransistor

OP505, OP506, OP535 & OP705 Series



Electrical Specifications

Electrical Characteristics (T _A = 25° C unless otherwise noted)						
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Photodarlington (OP535)						
I _{C(ON)}	On-State Collector Current OP535C OP535B OP535A	1.5 3.5 10.5	- - -	- 32.0 -	mA	$V_{CE} = 5 \text{ V, } E_E = 0.13 \text{ mW/cm}^{2 \text{ (1)}}$
I _{CEO}	Collector-Dark Current	-	-	100	nA	V _{CE} = 10 V, E _E = 0
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	15.0	-	-	V	I _C = 1.0 mA, E _E = 0
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0	-	-	V	I _E = 100 μA, E _E = 0
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	-	-	1.10	V	$I_C = 250 \mu\text{A}, E_E = 5 \text{mW/cm}^{2 (1)(2)}$

Notes:

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⁽¹⁾ Light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm and a radiometric intensity level, which varies less than 10% over the entire lens surface of the phototransistor being tested.

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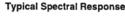
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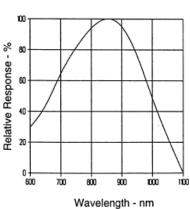
OP505, OP506, OP535 & OP705 Series

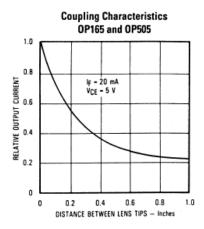


Performance

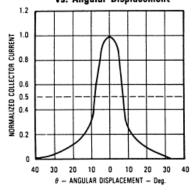
OP505A, OP505B, OP505C, OP505D



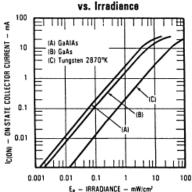




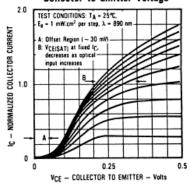
Normalized Collector Current vs. Angular Displacement



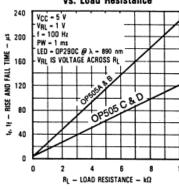
On-State Collector Current



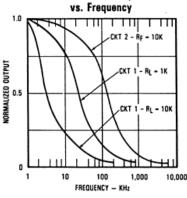
Normalized Collector Current vs. Collector to Emitter Voltage



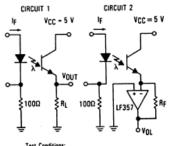
Rise and Fall Time vs. Load Resistance



Normalized Output



Switching Time Test Circuit



Test Conditions: Light source is pulsed LED with t_c and $t_f \le 500$ m t_p is adjusted for $V_{OUT} = 1$ Volt.

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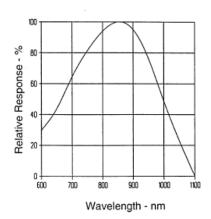
OP505, OP506, OP535 & OP705 Series



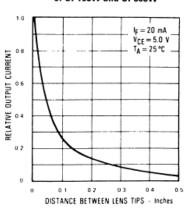
Performance

OP505W

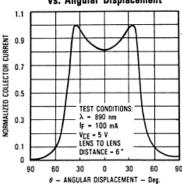
Typical Spectral Response



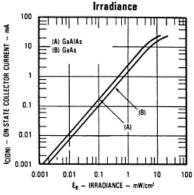
Coupling Characteristics of OP165W and OP505W



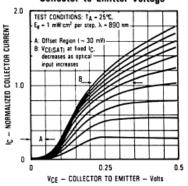
Normalized Collector Current vs. Angular Displacement



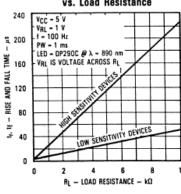
On-State Collector Current vs



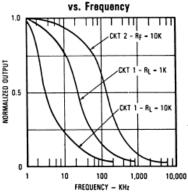
Normalized Collector Current vs. Collector to Emitter Voltage



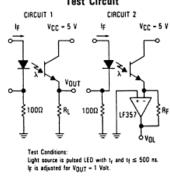
Rise and Fall Time vs. Load Resistance



Normalized Output



Switching Time **Test Circuit**



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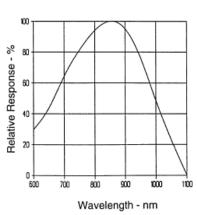
OP505, OP506, OP535 & OP705 Series

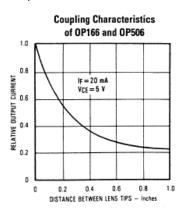


Performance

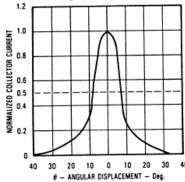
OP506A, OP506B, OP506C, OP506D



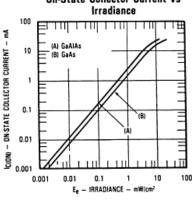




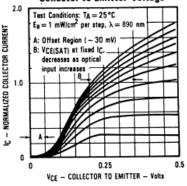
Normalized Collector Current vs Angular Displacement



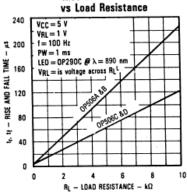
On-State Collector Current vs Irradiance



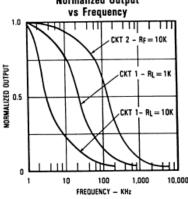
Normalized Collector Current vs Collector-to-Emitter Voltage



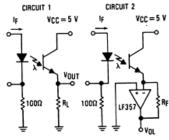
Rise and Fall Time



Normalized Output



Switching Time Test Circuit



Test Conditions: Light source is pulsed LED with t_f and $t_f \leq 500$ ns. IF is adjusted for VOUT = 1 Volt.

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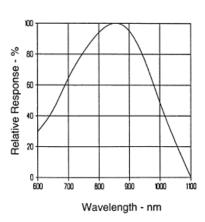
OP505, OP506, OP535 & OP705 Series



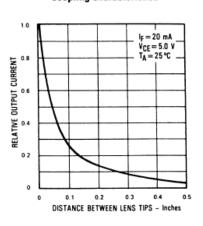
Performance

OP506W

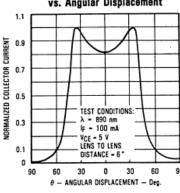




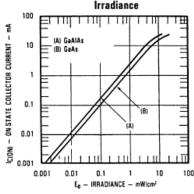
Coupling Characteristics



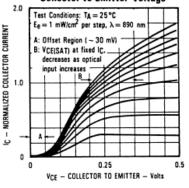
Normalized Collector Current vs. Angular Displacement



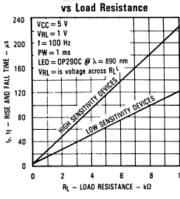
On-State Collector Current vs Irradiance



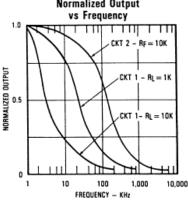
Normalized Collector Current vs Collector-to-Emitter Voltage



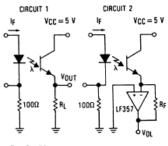
Rise and Fall Time



Normalized Output



Switching Time **Test Circuit**



Light source is pulsed LED with t_f and $t_f \le 500$ ns. IF is adjusted for VOLIT = 1 Volt.

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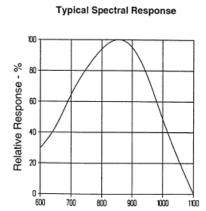
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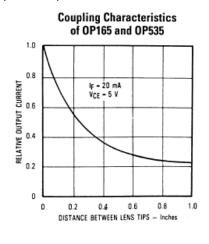
OP505, OP506, OP535 & OP705 Series

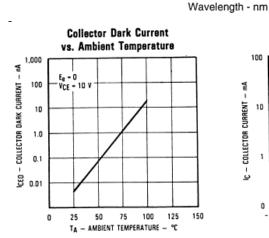


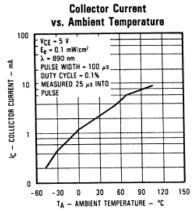
Performance

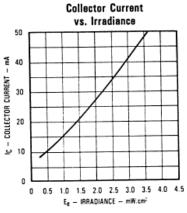
OP535A, OP535B, OP535C, OP535D

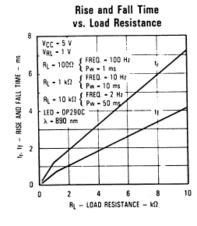


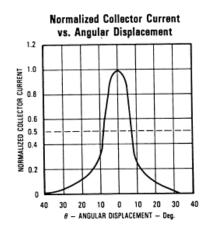


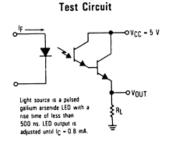












Switching Time

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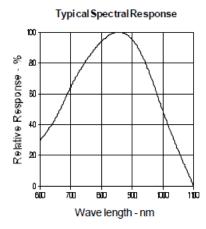
OP505, OP506, OP535 & OP705 Series

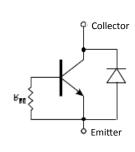


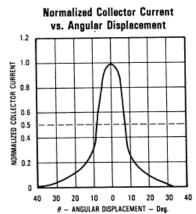
Performance

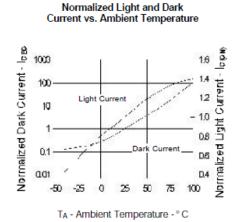
OP705A, OP705B, OP705C, OP705D

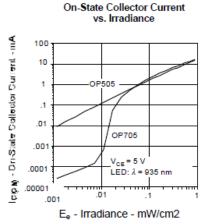
Schematic

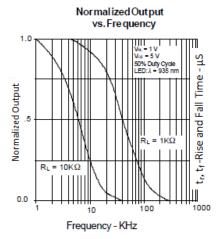


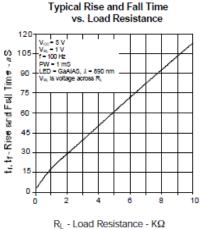


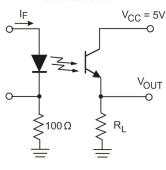












Switching Time

Test Circuit

Test Conditions:
Light Source is pulsed LED with tr and tf ≤ 500nS.
IF is adjusted for V_{OUT} = 1Volt.

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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